Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1.5 kV HBM (class H1C)
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	-	17	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C		-	-	19	W
Static chara	acteristics		'	'			
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5.5 \text{ A}; T_j = 25 \text{ °C}$		-	29	38	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	15776	D
2	D	drain		
3	G	gate	2 5	G ✓ ↓ ★ \
4	S	source	3 8 4	【 本 <u> </u>
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	s
7	D	drain		017aaa255
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK6D38-30E		plastic, leadless thermal enhanced ultra thin small outline package; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK6D38-30E	6B

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	17	А
		V _{GS} = 10 V; T _{sp} = 100 °C		-	12	Α
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	5.5	А
I _{DM}	peak drain current	T_{sp} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	68	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C		-	19	W
		T _{amb} = 25 °C	[1]	-	2	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain	diode			<u>'</u>		
Is	source current	T _{sp} = 25 °C		-	17	Α
		T _{amb} = 25 °C	[1]	-	2	Α
I _{SM}	peak source current	single pulse; $t_p \le 10 \mu s$; $T_{sp} = 25 °C$		-	68	Α
ESD maximu	m rating			<u> </u>	'	
V_{ESD}	electrostatic discharge voltage	НВМ	[2]	-	1500	V
Avalanche ru	ggedness		'			_
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.67 A; DUT in avalanche (unclamped)		-	10	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Measured between all pins.

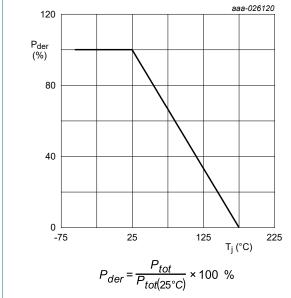


Fig. 1. Normalized total power dissipation as a function of junction temperature

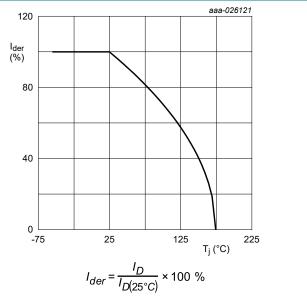


Fig. 2. Normalized continuous drain current as a function of junction temperature

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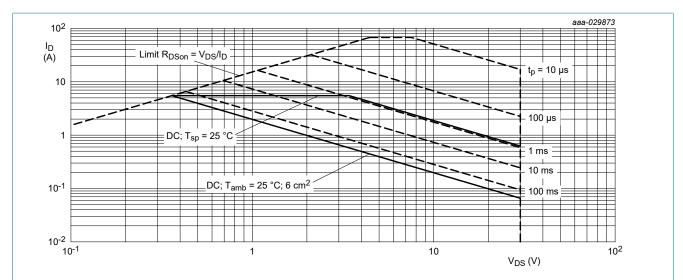


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	4	8	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

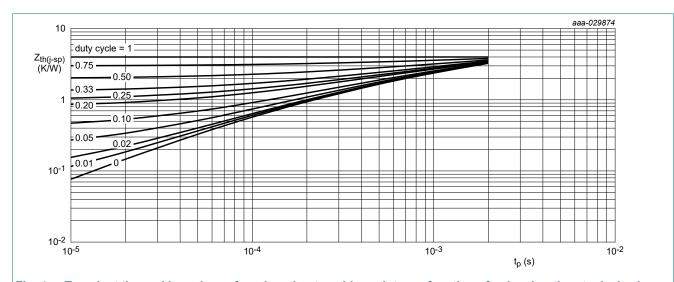


Fig. 4. Transient thermal impedance from junction to solder point as a function of pulse duration; typical values

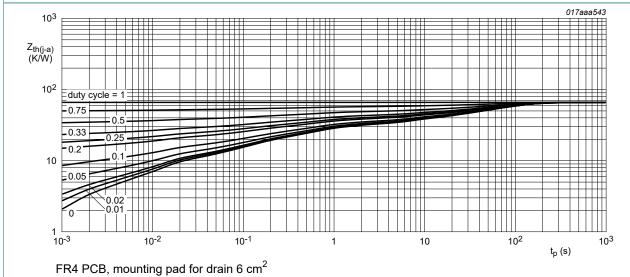


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 125 °C	-	-	20	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5.5 A; T _j = 25 °C	-	29	38	mΩ
		V _{GS} = 10 V; I _D = 5.5 A; T _j = 175 °C	-	50	65	mΩ
		V _{GS} = 4.5 V; I _D = 4.6 A; T _j = 25 °C	-	38	54	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 5.5 \text{ A}; T_j = 25 \text{ °C}$	-	10	-	S
R _G	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 5.5 A; V _{GS} = 10 V;	-	5.3	8	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.7	-	nC
Q_{GD}	gate-drain charge		-	1.2	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	266	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	70	-	pF
C _{rss}	reverse transfer capacitance		-	42	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 5.5 A; V _{GS} = 10 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	16	-	ns
t _{d(off)}	turn-off delay time		-	10	-	ns
t _f	fall time		-	4	-	ns
Source-dra	in diode		1			
V _{SD}	source-drain voltage	$I_S = 2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 1 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$	-	9	-	ns
Q _r	recovered charge	V _{DS} = 15 V; T _j = 25 °C	-	2	-	nC

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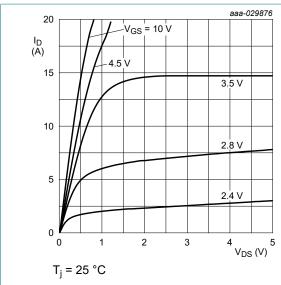


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

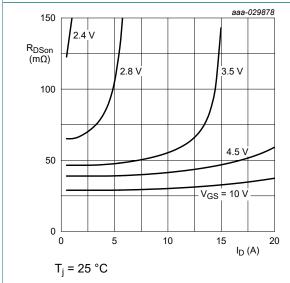


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

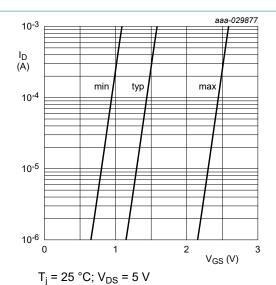


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

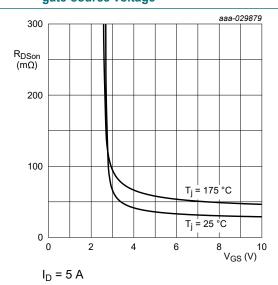


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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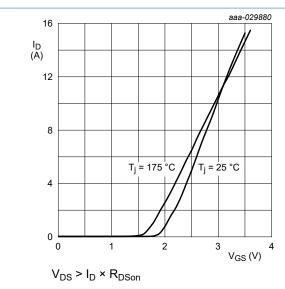


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

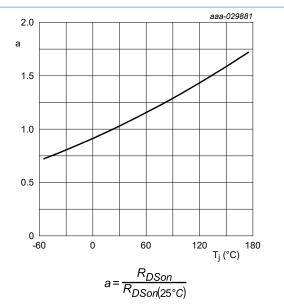


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

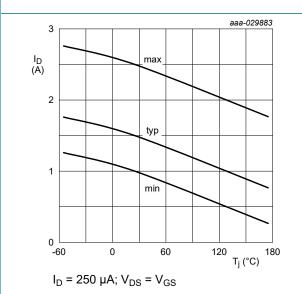


Fig. 12. Gate-source threshold voltage as a function of junction temperature

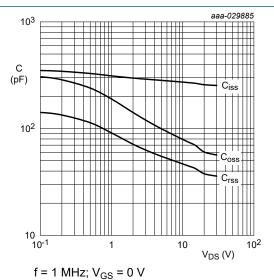


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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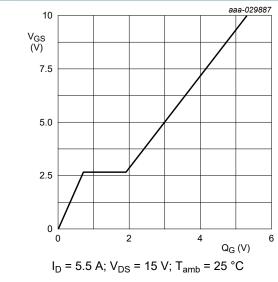


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

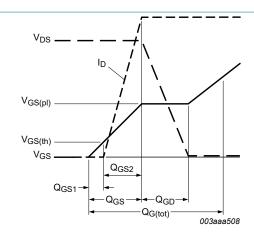


Fig. 15. Gate charge waveform definitions

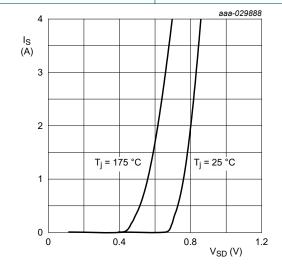
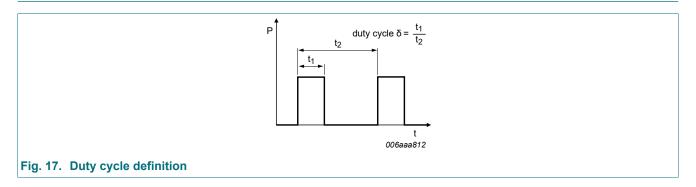


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information

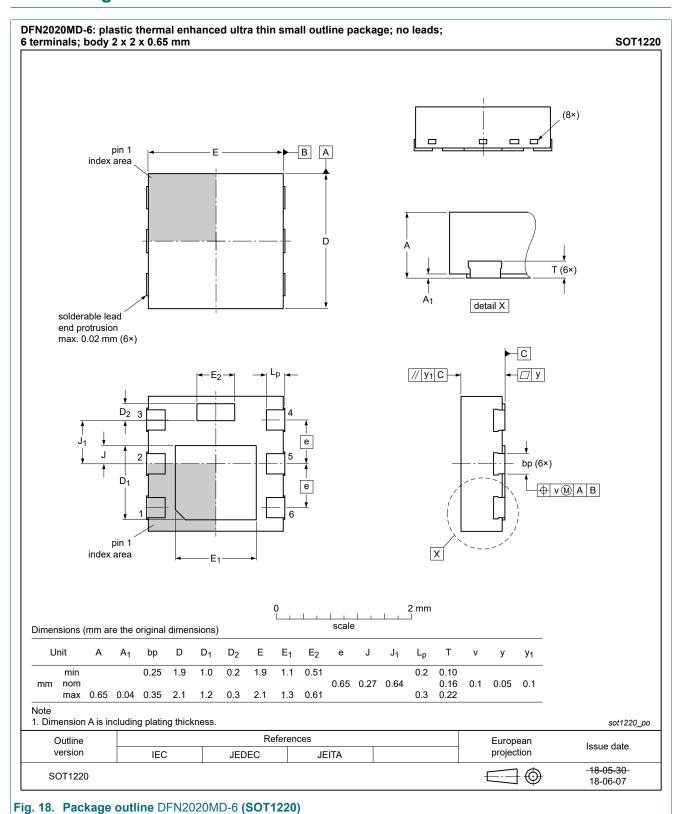


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

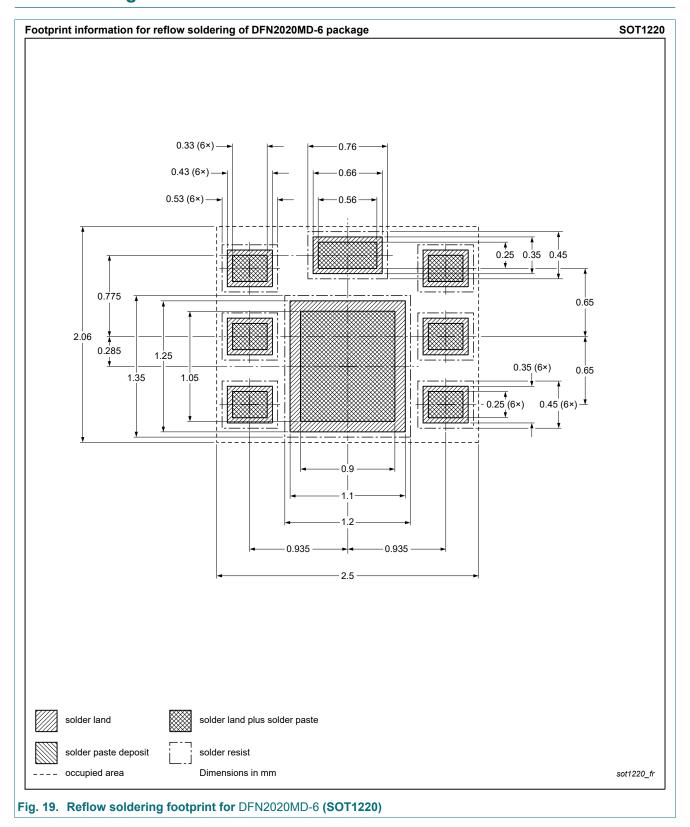
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BUK6D38-30E v.1	20190412	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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